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	Application No.	Applicant(s)
Notice of Allowability	09/574,653	KIM ET AL.
	Examiner	Art Unit
	Hsien-ming Lee	2823
The MAILING DATE of this communication appeal All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED or other appropriate comm IGHTS. This application is	in this application. If not included nunication will be mailed in due course. THIS
1. This communication is responsive to 12/22/2004.		
2. The allowed claim(s) is/are 1-3 and 9-12.		
3. \boxtimes The drawings filed on <u>03 January 2002</u> are accepted by th	e Examiner.	
 4. ☐ Acknowledgment is made of a claim for foreign priority up a) ☐ All b) ☐ Some* c) ☐ None of the: 1. ☐ Certified copies of the priority documents have 		or (f).
2. Certified copies of the priority documents have been received in Application No		
3. Copies of the certified copies of the priority documents have been received in this national stage application from the		
International Bureau (PCT Rule 17.2(a)).		
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which giv	nitted. Note the attached EX res reason(s) why the oath	CAMINER'S AMENDMENT or NOTICE OF or declaration is deficient.
6. CORRECTED DRAWINGS (as "replacement sheets") mu	st be submitted.	
(a) ☐ including changes required by the Notice of Draftsper	son's Patent Drawing Revie	ew (PTO-948) attached
1) ☐ hereto or 2) ☐ to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner Paper No./Mail Date	's Amendment / Comment o	or in the Office action of
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the		
7. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT	osit of BIOLOGICAL MATERIAL FOR THE DEPOSIT OF B	FERIAL must be submitted. Note the IOLOGICAL MATERIAL.
Attachment(s)		
1. Notice of References Cited (PTO-892)	5. Notice of I	nformal Patent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)		Summary (PTO-413), ./Mail Date
3. Information Disclosure Statements (PTO-1449 or PTO/SB/Paper No./Mail Date		s Amendment/Comment
4. ☐ Examiner's Comment Regarding Requirement for Deposit		s Statement of Reasons for Allowance
of Biological Material	9. 🗌 Other	
		HSIEN-MING LEE PRIMARY EXAMINED
		2/3/wus

Art Unit: 2823

DETAILED ACTION

Remarks

1. The 112-second-paragraph and 103(a) rejections have withdrawn in response to applicant's arguments filed 12/22/2004.

Examiner's Amendment

2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Peter McLarty (Reg. No. 44,923) on Feb.22, 2005.

3. The application has been amended as follows:

In claim 1, at line 7, replace "similar widths" with -- a first width --; and at lines 10-11, replace "the width" with -- a width --.

Cancel non-elected claims 13-19.

Allowable Subject Matter

- 4. Claims 1-3 and 9-12 are allowed.
- 5. The following is an examiner's statement of reasons for allowance:

Applicant's arguments, filed 12/22/2004, stated on pages 8-10 are persuasive. In particular, Masuoka does not teach or suggest etching an initial single layer sidewall structure adjacent to NMOS transistor gate structure such that a width of a first single layer sidewall structure adjacent to the NMOS transistor gate structure is less than a width of a second single

Application/Control Number: 09/574,653

Art Unit: 2823

layer sidewall structure adjacent to PMOS transistor gate structure. Furthermore, Masuoka does not teach or suggest forming LDD regions adjacent the first transistor gate stack and adjacent the second transistor gate stack. Thus, the instant is neither anticipated nor rendered obvious over the prior art of record.

- 6. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."
- Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hsien-ming Lee whose telephone number is 571-272-1863. The examiner can normally be reached on Tuesday-Thursday (8:00 ~ 6:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hsien-ming Lee Primary Examiner Art Unit 2823

HSIEN-MING LEE PRIMARY EXAMINER

Page 3

2/3/2005